



DMTH4007SK3

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
40V	6mΩ @ V _{GS} = 10V	80A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management Functions
- DC-DC Converters
- Backlighting

40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On State Losses are Minimized
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

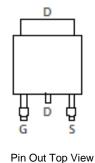
Mechanical Data

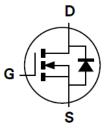
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ⁽²⁾
- Weight: 0.33 grams (Approximate)



TO252 (DPAK)

Top View





Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4007SK3-13	TO252 (DPAK)	2,500/Tape & Reel

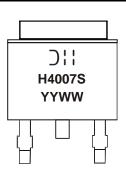
EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



D'I' = Manufacturer's Marking
H4007S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	T _A = +25°C T _A = +100°C	ID	17.6 12.5	A
Continuous Drain Current, V _{GS} = 10V (Note 6)	T _C = +25°C T _C = +100°C	ID	76 54	A
Maximum Continuous Body Diode Forward Current (Note 6)	Is	60	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	100	A	
Avalanche Current, L=0.3mH	IAS	20	A	
Avalanche Energy, L=0.3mH	E _{AS}	60	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	47	°C/W
Total Power Dissipation (Note 6)	PD	59	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	2.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

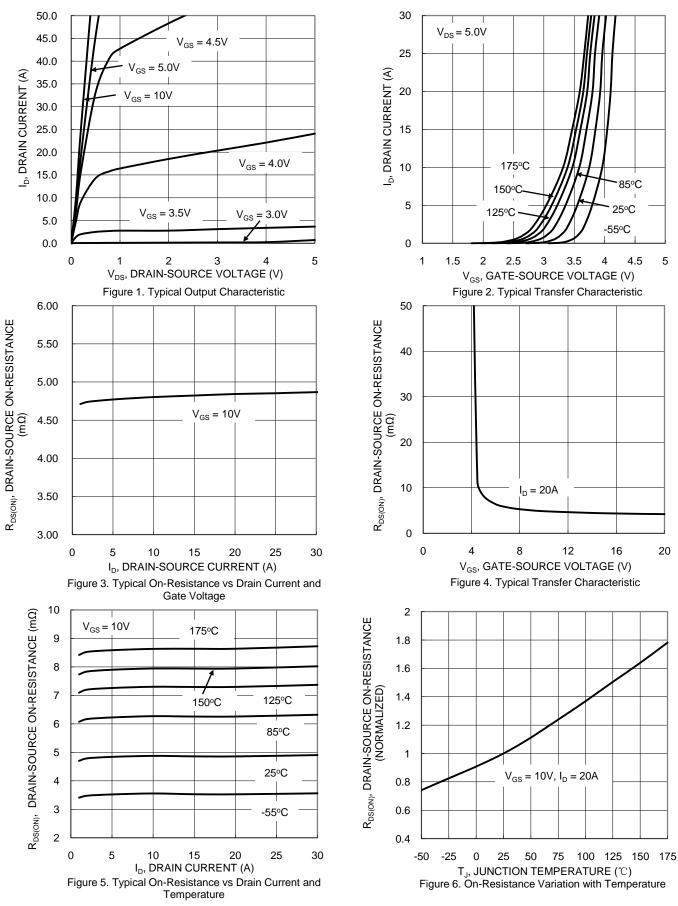
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						-	
Drain-Source Breakdown Voltage	BV _{DSS}	40	-	-	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	-	4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	6	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	-	-	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)			-			-	
Input Capacitance	Ciss	-	2082	-		$V_{DS} = 25V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	-	790	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	113	-			
Gate Resistance	Rg	-	0.46	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	-	41.9	-			
Gate-Source Charge	Qgs	-	10	-	nC	$V_{DS} = 30V, I_D = 20A, V_{GS} = 10V$	
Gate-Drain Charge	Q _{gd}	-	11.5	-			
Turn-On Delay Time	t _{D(ON)}	-	7	-			
Turn-On Rise Time	t _R	-	11.5	-		$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 20A, R_G = 3\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	-	15.6	-	ns		
Turn-Off Fall Time	tF	-	8.8	-			
Body Diode Reverse Recovery Time	t _{RR}	-	29.9	-	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	-	23	-	nC	I _F = 20A, di/dt = 100A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



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 $I_D = 1mA$

f = 1MHz

25

P

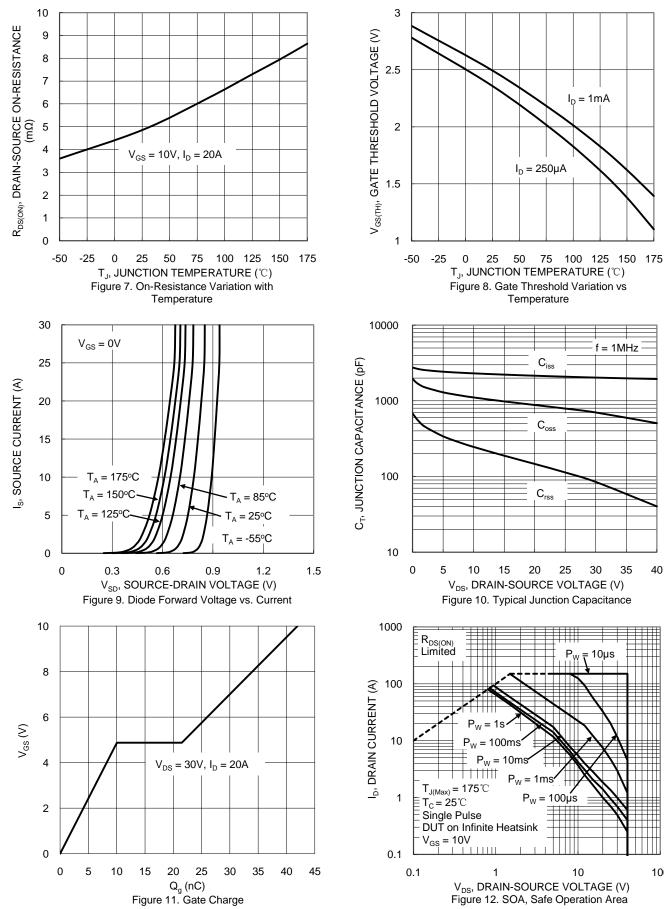
10

30

: 10µs

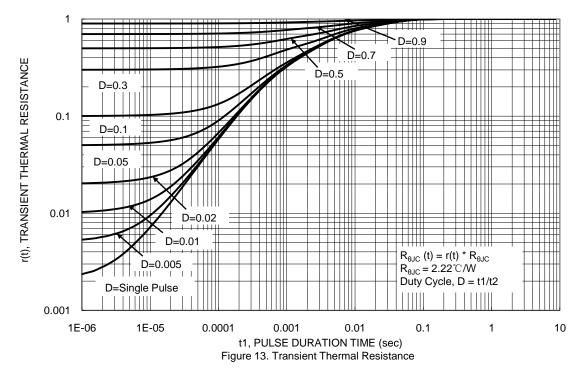
35

40



100



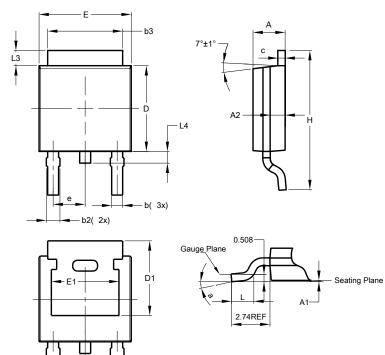




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

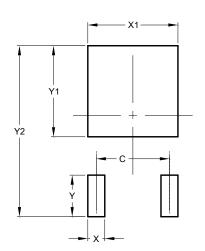


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Ε	6.45	6.70	6.58		
E1	4.32	-	-		
Η	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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